

SIHP11N80E-GE3

SIHP11N80E-GE3 Information

Www.heisence.com	 SIHP11N80E-GE3 Vishay Siliconix Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CHAN 850V TO-220AB TO-220-3 For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



SIHP11N80E-GE3 Specifications

Manufacturer Part Number	SIHP11N80E-GE3
Manufacturer	Vishay Siliconix
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-220-3
Series	Ε
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	800V
Current - Continuous Drain (Id) @ 25°C	12A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	88nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	1670pF @ 100V
Vgs (Max)	±30V
FET Feature	-
Power Dissipation (Max)	179W (Tc)
Rds On (Max) @ Id, Vgs	440 mOhm @ 5.5A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Supplier Device Package	TO-220AB
Package / Case	TO-220-3
	Report errors?

SIHP11N80E-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

SIHP11N80E-GE3 Payment Methods



SIHP11N80E-GE3 Shipping Methods



If you have any question about SIHP11N80E-GE3, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com